

# MMBT2222AWT1G, SMMBT2222AWT1G

## General Purpose Transistor

### NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

#### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	75	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	600	mAdc

#### THERMAL CHARACTERISTICS

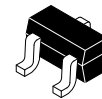
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	280	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

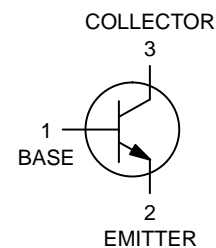


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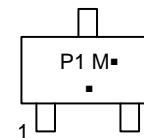
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SC-70  
CASE 419  
STYLE 3



#### MARKING DIAGRAM



P1 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT2222AWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBT2222AWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	75	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	V <sub>dc</sub>
Base Cutoff Current (V <sub>CE</sub> = 60 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> )	I <sub>BL</sub>	–	20	nA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 60 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> )	I <sub>CEx</sub>	–	10	nA <sub>dc</sub>

## ON CHARACTERISTICS (Note 1)

DC Current Gain (Note 1) (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 150 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> )	H <sub>FE</sub>	35 50 75 100 40	– – – 300 –	–
Collector–Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.3 1.0	V <sub>dc</sub>
Base–Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	0.6 –	1.2 2.0	V <sub>dc</sub>

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain–Bandwidth Product (I <sub>C</sub> = 20 mA <sub>dc</sub> , V <sub>CE</sub> = 20 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	300	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	30	pF
Input Impedance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	0.25	1.25	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>re</sub>	–	4.0	X 10 <sup>–4</sup>
Small–Signal Current Gain (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	75	375	–
Output Admittance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	25	200	μmhos
Noise Figure (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 100 μA <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 V <sub>dc</sub> , V <sub>BE</sub> = –0.5 V <sub>dc</sub> , I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B1</sub> = 15 mA <sub>dc</sub> )	t <sub>d</sub>	–	10	ns
Rise Time		t <sub>r</sub>	–	25	
Storage Time	(V <sub>CC</sub> = 30 V <sub>dc</sub> , I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B1</sub> = I <sub>B2</sub> = 15 mA <sub>dc</sub> )	t <sub>s</sub>	–	225	ns
Fall Time		t <sub>f</sub>	–	60	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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## SWITCHING TIME EQUIVALENT TEST CIRCUITS

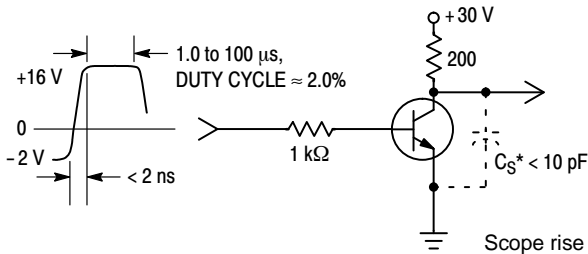


Figure 1. Turn-On Time

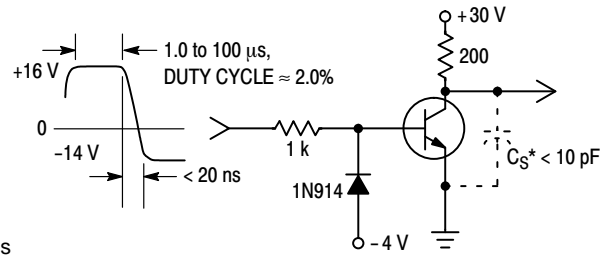


Figure 2. Turn-Off Time

Scope rise time < 4 ns  
\*Total shunt capacitance of test jig, connectors, and oscilloscope.

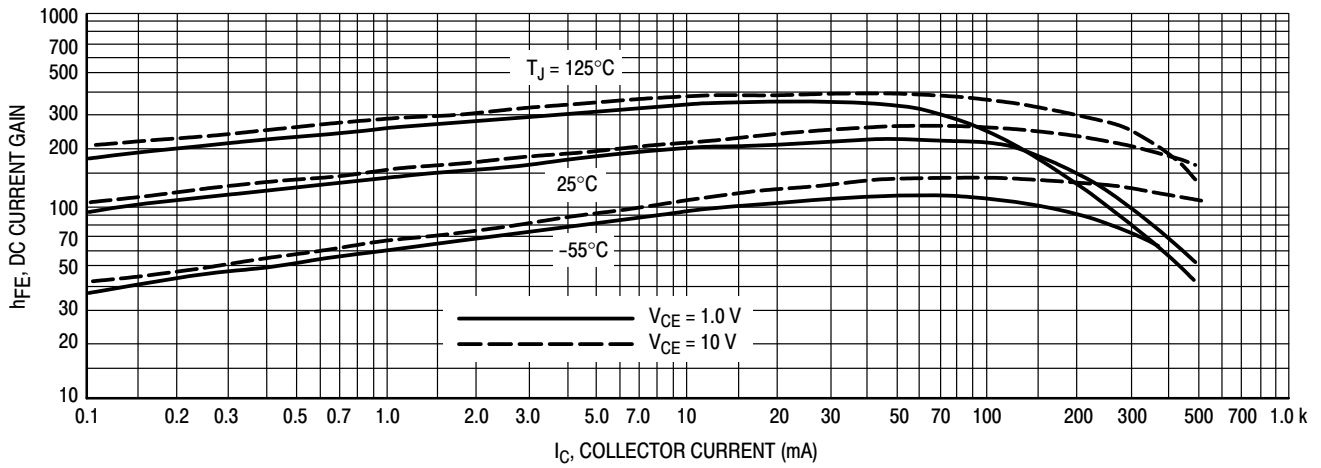


Figure 3. DC Current Gain

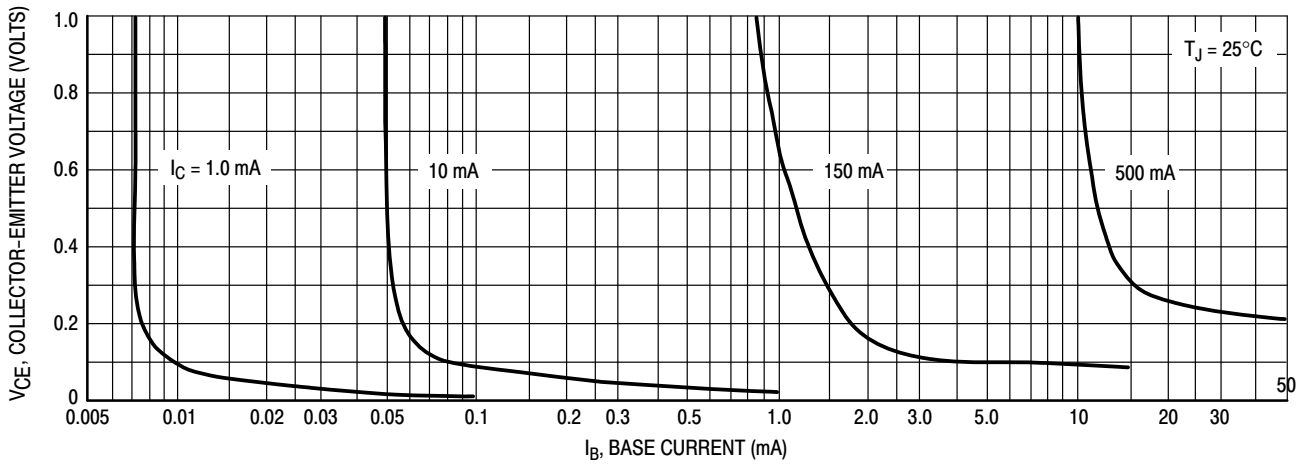


Figure 4. Collector Saturation Region

# MMBT2222AWT1G, SMMBT2222AWT1G

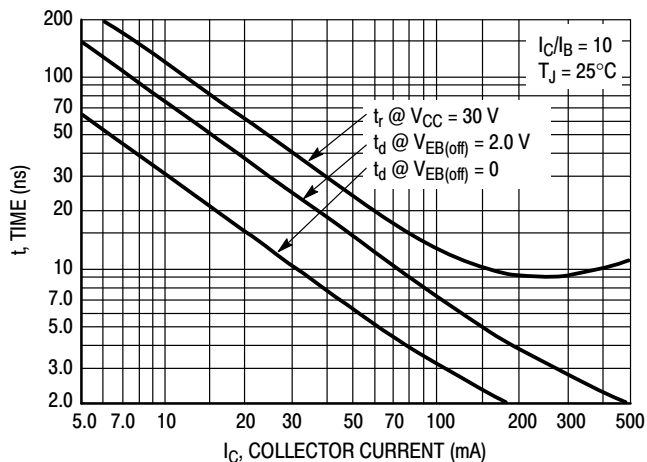


Figure 5. Turn-On Time

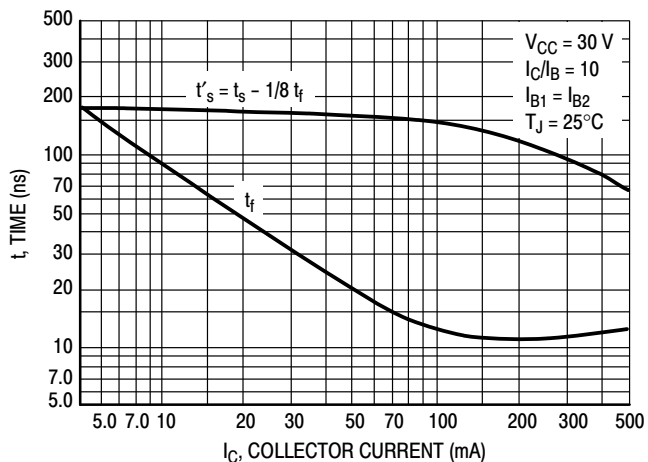


Figure 6. Turn-Off Time

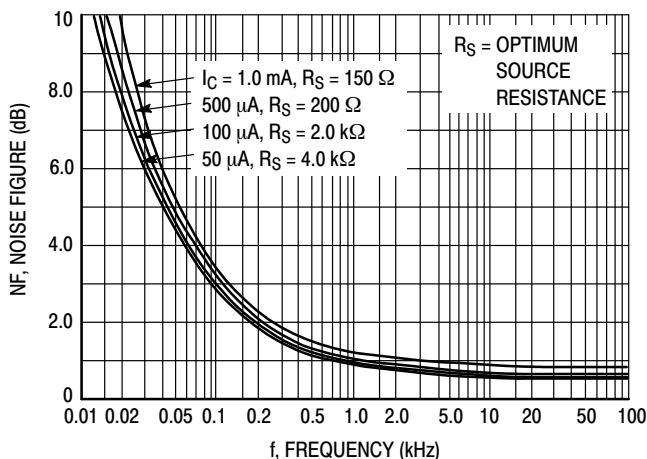


Figure 7. Frequency Effects

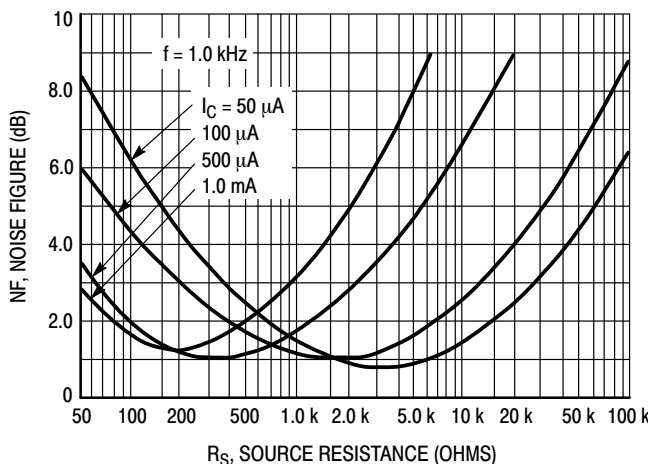


Figure 8. Source Resistance Effects

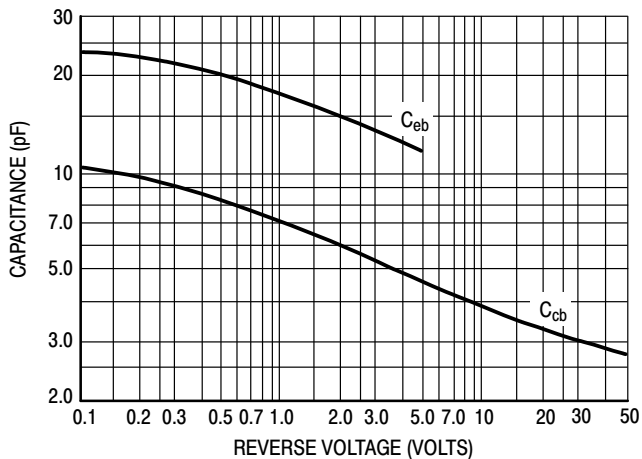


Figure 9. Capacitances

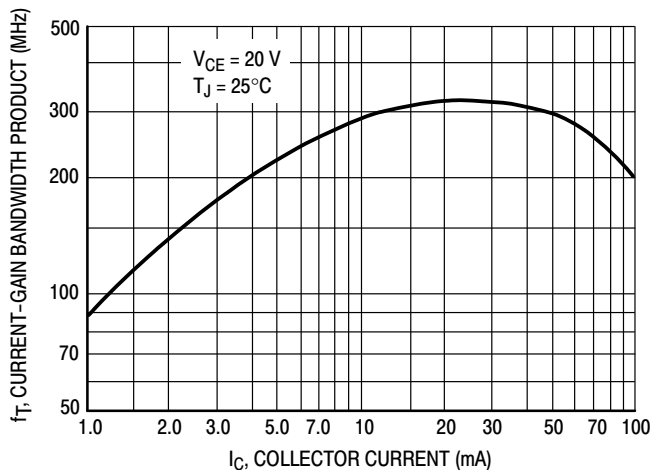
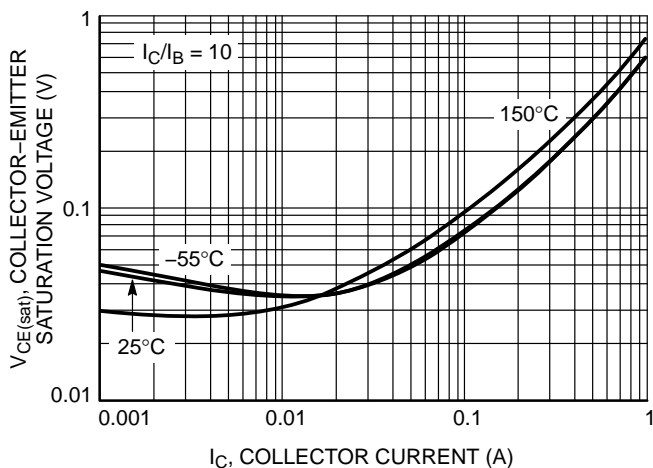
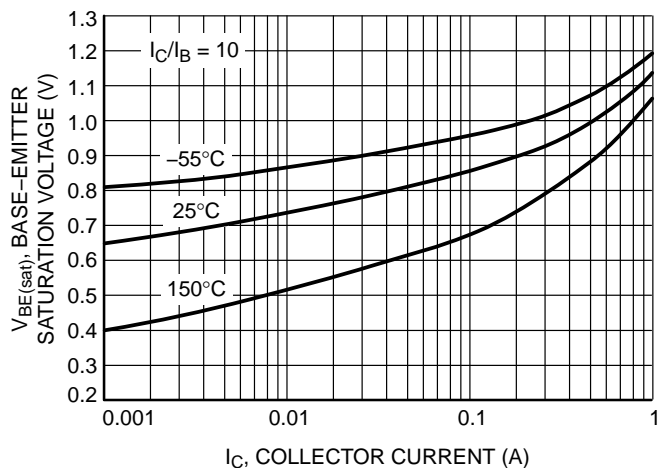


Figure 10. Current-Gain Bandwidth Product

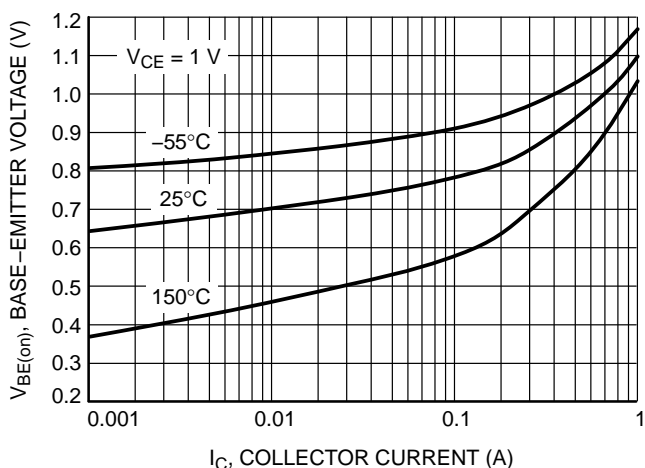
# MMBT2222AWT1G, SMMBT2222AWT1G



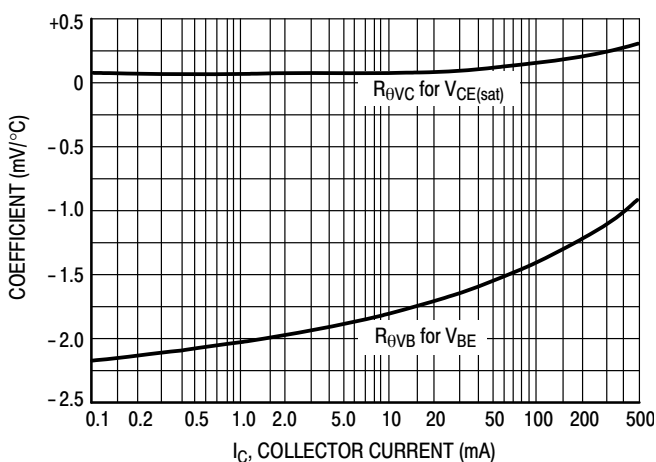
**Figure 11. Collector Emitter Saturation Voltage vs. Collector Current**



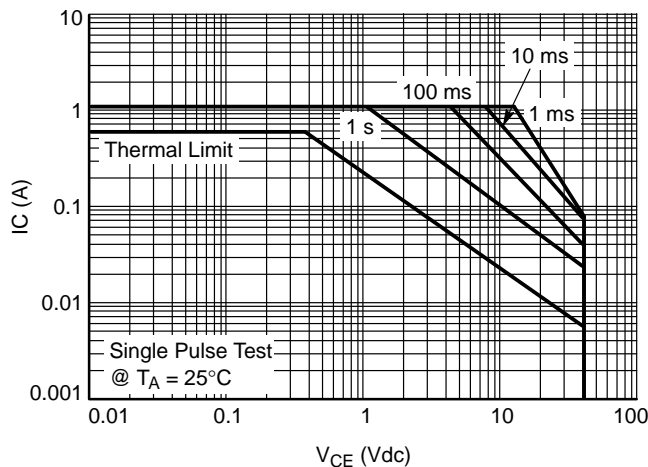
**Figure 12. Base Emitter Saturation Voltage vs. Collector Current**



**Figure 13. Base Emitter Voltage vs. Collector Current**



**Figure 14. Temperature Coefficients**



**Figure 15. Safe Operating Area**

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



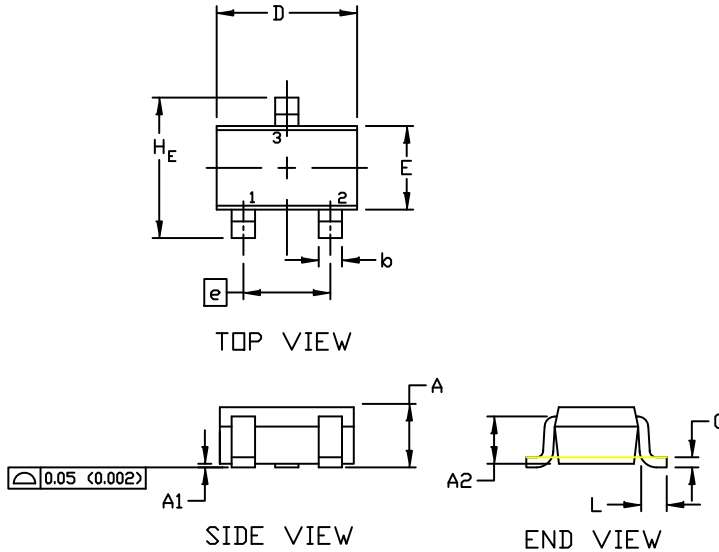
SCALE 4:1

SC-70 (SOT-323)  
CASE 419  
ISSUE P

DATE 07 OCT 2021

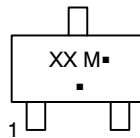
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH



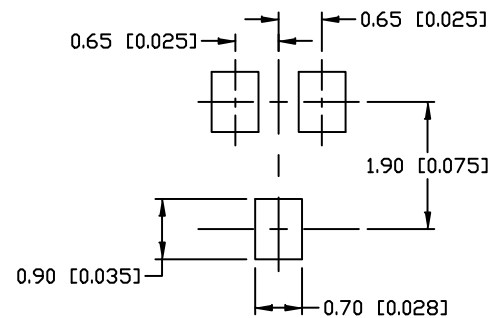
DIM	MILLIMETERS			INCHES		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- |   |   |   |  |   |   |
|---|---|---|--|---|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |   |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE |

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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